AMENDMENT TO THE CLAIMS

Claims 1-32 (cancelled).

33. (New) A semiconductor light-emitting device comprising:

an n-side electrode;

a p-side electrode;

an n-type nitride semiconductor portion electrically connected to said n-side electrode;

a p-type nitride semiconductor portion electrically connected to said p-side electrode; and

an active layer, sandwiched between said n-type nitride semiconductor portion and said p-type nitride semiconductor portion, for generating emission light, wherein

said n-side electrode is a divided electrode comprising a plurality of conductive members spaced apart from each other.

34. (New) The semiconductor light-emitting device according to claim 33, wherein

said divided electrode is in contact with said n-type nitride semiconductor portion.

35. (New) The semiconductor light-emitting device according to claim 33, wherein

said p-side electrode is formed in a linear shape in plan view, and

said n-side electrode is formed so as to be entirely parallel to said p-side electrode.

36. (New) The semiconductor light-emitting device according to claim 35, wherein

said divided electrode is divided in a longitudinal direction of said p-side electrode.

37. (New) The semiconductor light-emitting device according to claim 35, further comprising a substrate, wherein,

said n-type nitride semiconductor portion is provided on a surface of the substrate and is sandwiched between said each divided electrode and said substrate.

38. (New) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed at an angle of 90° to said p-type electrode in plan view.

39. (New) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed at an angle of θ ($0° < \theta < 90°$) to said p-type electrode in plan view.

40. (New) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed in a zigzag shape.

41. (New) The semiconductor light-emitting device according to claim 35, wherein a dividing region in a linear shape disposed between said divided electrodes is formed in a curved shape.

42. (New) The semiconductor light-emitting device according to claim 33, wherein said divided electrodes sandwich said p-side electrode, and said divided electrodes and said p-side electrode are spaced apart respectively in plan view.

43. (New) The semiconductor light-emitting device according to claim 42, wherein said divided electrodes are formed so as to be asymmetrical in plan view with respect to said p-side electrode.

44. (New) The semiconductor light-emitting device according to claim 42, wherein one of said divided electrodes is not disposed at a portion opposite to the other divided electrode with said p-side electrode being interposed therebetween.

45. (New) The semiconductor light-emitting device according to claim 44, wherein

said divided electrodes are adapted such that each have an overlapping portion that overlaps the other at their ends adjacent to each other in a direction perpendicular to the p-side electrode in the plane thereof in plan view.

46. (New) The semiconductor light-emitting device according to claim 33, further comprising a substrate, wherein

said substrate is conductive,

said n-type nitride semiconductor portion is provided on a surface of said substrate, and

one of said divided electrodes is provided on a rear surface of said substrate.

47. (New) The semiconductor light-emitting device according to claim 46, wherein

said the other divided electrode is in contact with said n-type nitride semiconductor portion.

48. (New) A method for fabricating a semiconductor light-emitting device comprising the steps of:

growing successively an n-type nitride semiconductor portion, an active layer, and a p-type nitride semiconductor portion on a substrate, each substantially in a uniform thickness;

exposing part of said n-type nitride semiconductor portion to form then n-side electrode on said exposed n-type nitride semiconductor portion;

forming a p-side electrode on said p-type nitride semiconductor portion; and

forming a divided electrode by isolating said n-side electrode into a plurality of electrodes.

49. (New) The method for fabricating a semiconductor light-emitting device according to claim 48, wherein

said step of forming the divided electrode employs an etching method.

50. (New) The method for fabricating a semiconductor light-emitting device according to claim 48, wherein

said step of forming the divided electrode employs a lift-off method.

51. (New) A method for fabricating a semiconductor light-emitting device comprising the steps of:

growing successively an n-type nitride semiconductor portion, an active layer, and a p-type nitride semiconductor portion on a substrate, each substantially in a uniform thickness;

exposing part of said n-type nitride semiconductor portion to form then a first n-side electrode on said exposed n-type nitride semiconductor portion;

forming a second n-side electrode on a surface opposite to a surface of said substrate having said active layer; and

forming a p-side electrode on said p-type nitride semiconductor portion.